2SK3289

Silicon N Channel MOS FET High Speed Switching

HITACHI

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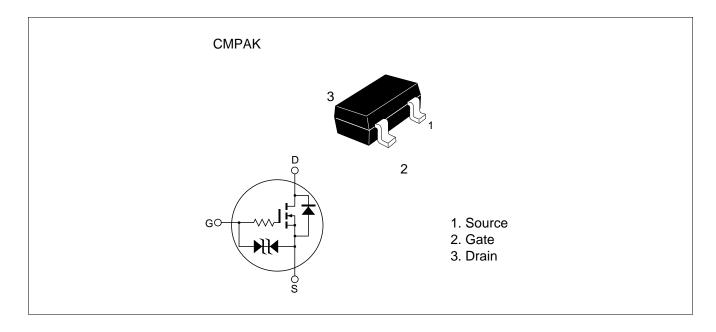
Features

• Low on-resistance

$$R_{DS}$$
 =1.26 Ω typ. (V $_{GS}$ = 10 V , I_D = 150 mA)
$$R_{DS}$$
 = 2.8 Ω typ. (V $_{GS}$ = 4 V , I_D = 50 mA)

- 4 V gate drive device.
- Small package (CMPAK)

Outline





2SK3289

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	$V_{\rm GSS}$	±20	V
Drain current	I _D	300	mA
Drain peak current	Note1	1.2	A
Body-drain diode reverse drain current	I _{DR}	300	mA
Channel dissipation	Pch Note 2	300	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value on the alumina ceramic board (12.5 x 20 x 0.7 mm)

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	_	_	V	$I_D = 100 \ \mu A, \ V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}			±5	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltege drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.3	_	2.3	V	$I_{D} = 10\mu A, V_{DS} = 5 V$
Static drain to source on state	$R_{\text{DS(on)}}$	_	1.26	3.44	Ω	$I_D = 150 \text{ mA}, V_{GS} = 10 \text{ V}^{\text{Note 3}}$
resistance	$R_{\text{DS(on)}}$	_	2.8	3.44	Ω	$I_D = 50 \text{ mA}, V_{GS} = 4 \text{ V}^{\text{Note 3}}$
Forward transfer admittance	y _{fs}	145	220		mS	$I_D = 150 \text{ mA}, V_{DS} = 10 \text{ V}^{\text{Note 3}}$
Input capacitance	Ciss		6		pF	V _{DS} = 10 V
Output capacitance	Coss		18		pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss		2	_	pF	f = 1 MHz
Turn-on delay time	$t_{\text{d(on)}}$		200		ns	$I_D = 150 \text{ mA}, V_{GS} = 10 \text{ V}$
Rise time	t _r		600		ns	$R_L = 66.6 \Omega$
Turn-off delay time	t _{d(off)}		1100	_	ns	
Fall time	t _f	_	1100	_	ns	

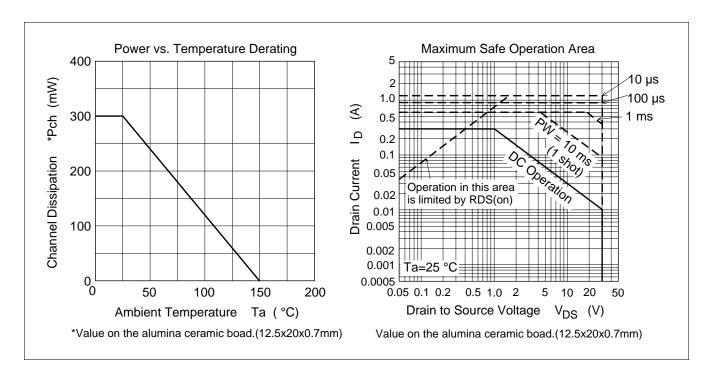
Note:

3. Pulse test

4. Marking is AN

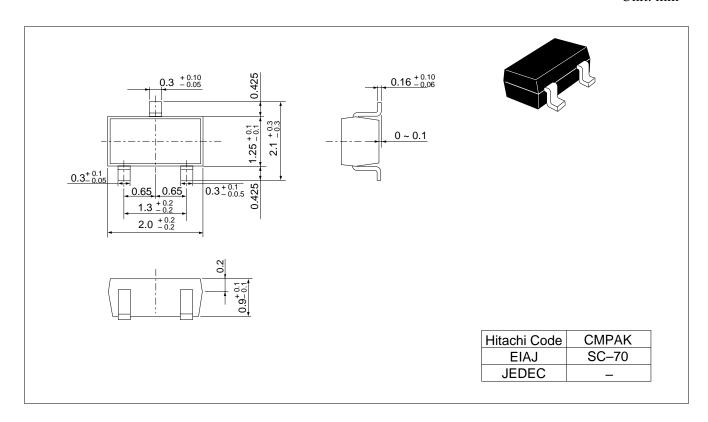
See characteristics curves of 2SK3287

Main Characteristics



Package Dimensions

Unit: mm



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